

L1050-66-60 epoxy lens type Infrared illuminator

L1050-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency GaAs diode chips, mounted on a metal stem TO-66 with AlN ceramics and covered with double coated clear silicone and epoxy resin. These devices are designed for high current operation with proper heat sinking to improve thermal conductive efficiency.

◆ Features

- 1) High reliability
- 2) Compact (TO-66) package
- 3) High output power at 1050nm

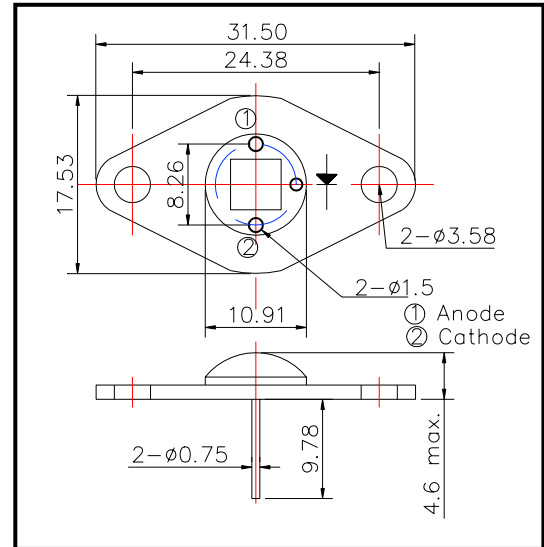
◆ Applications

- 1) For IR search light
- 2) For CCD lighting

◆ Specifications

- | | |
|---------------------|-------------------------------|
| 1) Product name | IR illuminator |
| 2) Spec. No. | L1050-66-60 |
| 3) Chip | |
| (1) Material | GaAs |
| (2) Peak wavelength | 1050m |
| 4) Package | |
| (1) Stem | TO-66 stem with AlN |
| (2) Lens | Clear silicone and epoxy lens |

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

| Item | Symbol | Maximum Rated Value | Unit | Ambient Temp. |
|-----------------------|------------------|---------------------|------|----------------------|
| Power Dissipation | P _D | 6.0 | W | T _a =25°C |
| Forward Current | I _F | 800 | mA | T _a =25°C |
| Reverse Voltage | V _R | 50 | V | T _a =25°C |
| Operating Temperature | T _{OPR} | -30 ~ +80 | °C | |
| Storage Temperature | T _{STG} | -30 ~ +110 | °C | |
| Soldering Temperature | T _{SOL} | 240 | °C | |

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

◆ Electro-Optical Characteristics

| Item | Symbol | Condition | Minimum | Typical | Maximum | Unit |
|----------------------|------------------|-----------------------|---------|---------|---------|------|
| Total Radiated Power | P _O | I _F =600mA | | 120 | | mW |
| Forward Voltage | V _F | I _F =600mA | | 7.0 | | V |
| Reverse Current | V _R | I _R =10μA | 30 | | | V |
| Peak Wavelength | λ _P | I _F =600mA | 1000 | 1050 | 1100 | nm |
| Half Width | Δλ | I _F =600mA | | 55 | | nm |
| Viewing Half Angle | θ _{1/2} | I _F =600mA | | ±60 | | deg. |
| Rise Time | t _f | I _F =100mA | | 15 | | ns |
| Fall Time | t _f | I _F =100mA | | 10 | | ns |

‡Heat sink is required thermal resistance <8K/W

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